

Features

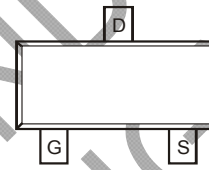
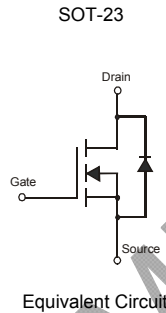
- Low On-Resistance:
 - $R_{DS(ON)} < 32m\Omega @ V_{GS} = 10V$
 - $R_{DS(ON)} < 42m\Omega @ V_{GS} = 4.5V$
 - $R_{DS(ON)} < 64m\Omega @ V_{GS} = 2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



TOP VIEW



Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 12	V
Drain Current (Note 1)	I_D	$T_A = 25^\circ C$	5.4
		$T_A = 70^\circ C$	4.6
Drain Current (Note 1)	I_{DM}	19	A
Body-Diode Continuous Current (Note 1)	I_S	2.0	A

Thermal Characteristics

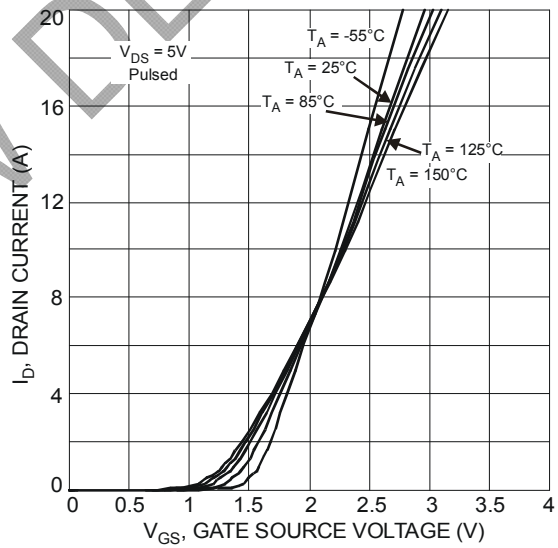
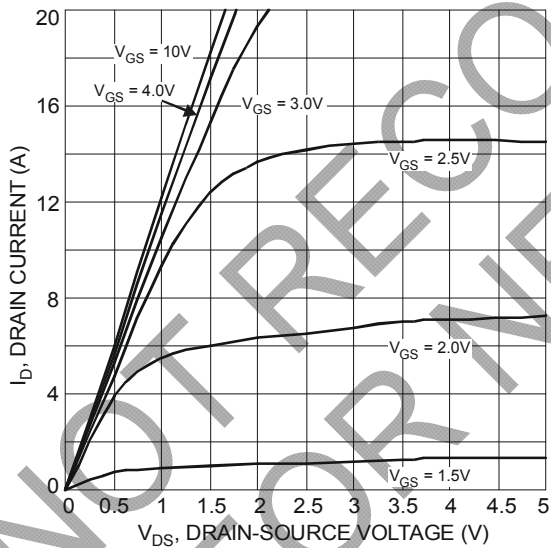
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	1.4	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 1)	$R_{\theta JA}$	90	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
1. Device mounted on FR-4 PCB. $t \leq 5$ sec.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	± 80 ± 800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	0.62	0.9	1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	26	32	$m\Omega$	$V_{GS} = 10V, I_D = 5.8A$
		—	33	42		$V_{GS} = 4.5V, I_D = 5.0A$
		—	52	64		$V_{GS} = 2.5V, I_D = 3.8A$
		—	78	100		$V_{GS} = 2.0V, I_D = 2.0A$
Forward Transconductance	$ Y_{fs} $	—	8	—	S	$V_{DS} = 5V, I_D = 3.1A$
Source-Drain Diode Forward Voltage	V_{SD}	—	0.75	1.2	V	$V_{GS} = 0V, I_S = 2.0A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	555	—	pF	$V_{DS} = 5V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	109	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	82	—	pF	
Total Gate Charge	Q_g	—	6.3	—	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_D = 5.8A$
Gate-Source Charge	Q_{gs}	—	1.3	—		
Gate-Drain Charge	Q_{gd}	—	1.7	—		

Notes: 4. Short duration pulse test used to minimize self-heating effect.



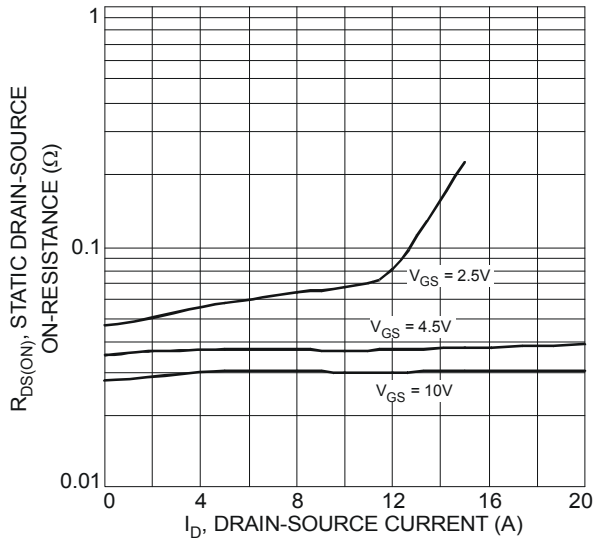


Fig 3 On-Resistance vs. Drain Current & Gate Voltage

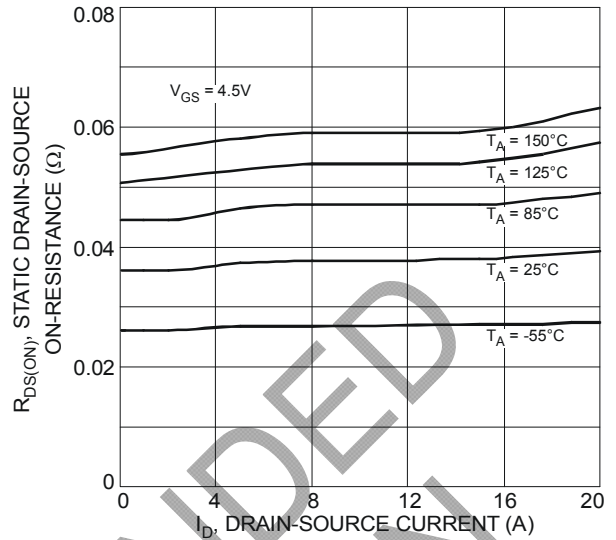


Fig 4 On-Resistance vs. Drain Current & Temperature

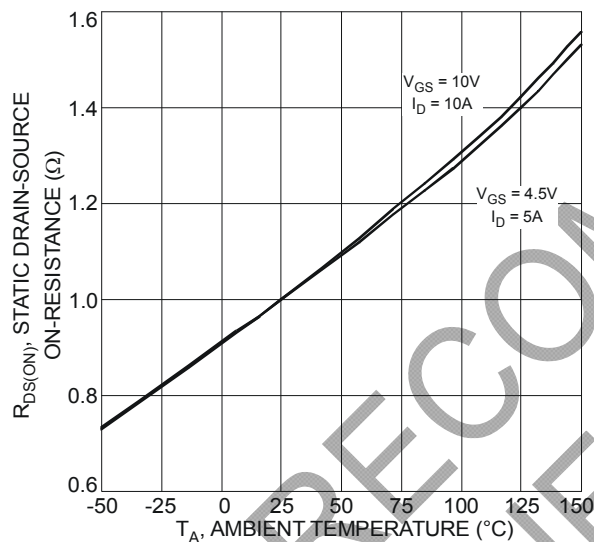


Fig 5 Static Drain-Source On-Resistance vs. Ambient Temperature

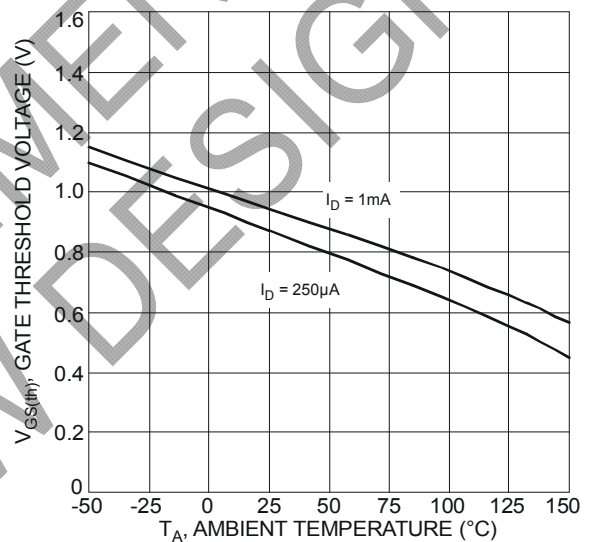


Fig 6 Gate Threshold Variation vs. Ambient Temperature

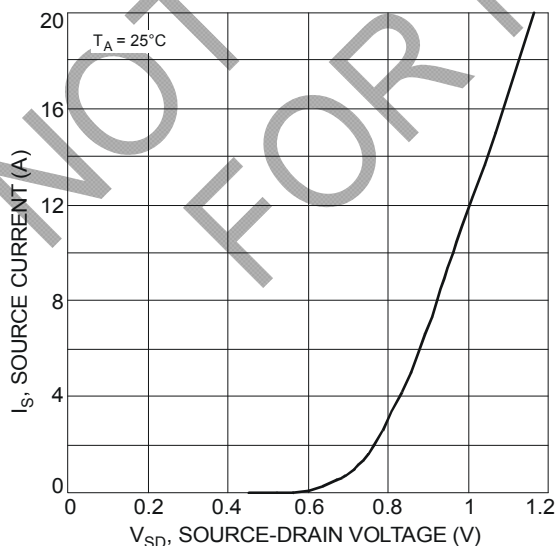


Fig 7 Reverse Drain Current vs. Source-Drain Voltage

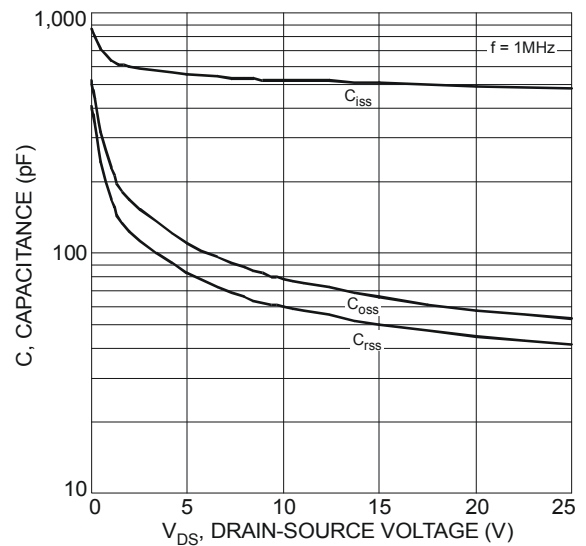
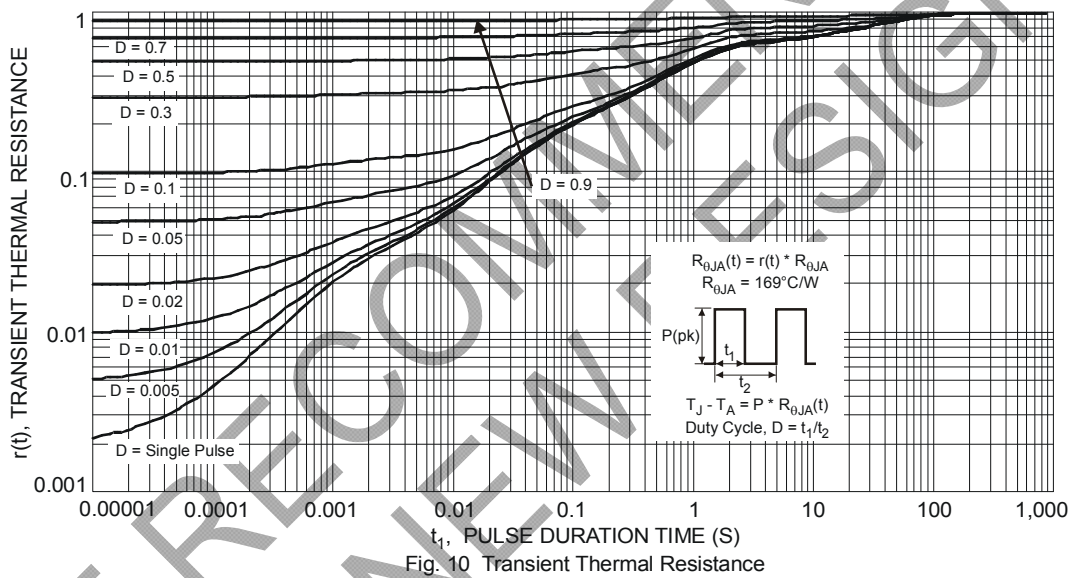
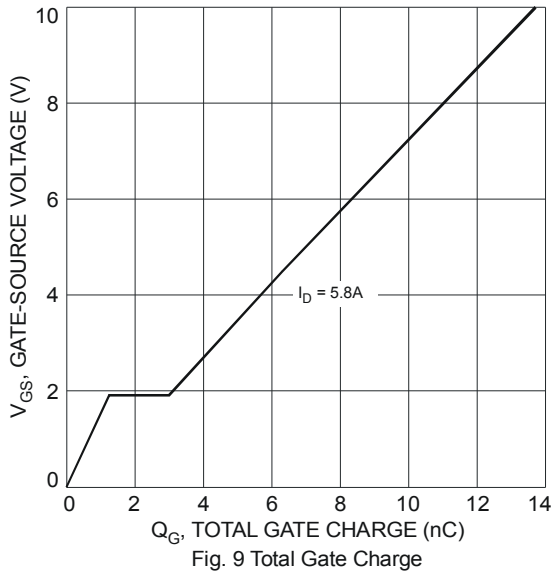


Fig 8 Typical Total Capacitance

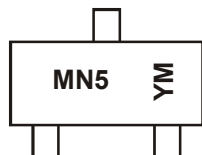


Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3052L-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



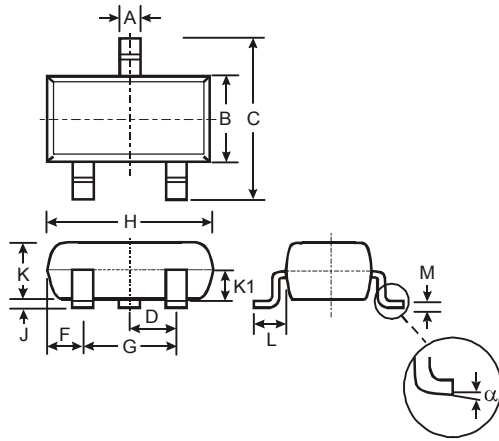
MN5 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: V = 2008)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

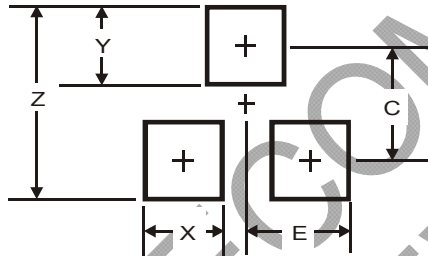
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

NOT RECOMMENDED FOR NEW DESIGN

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